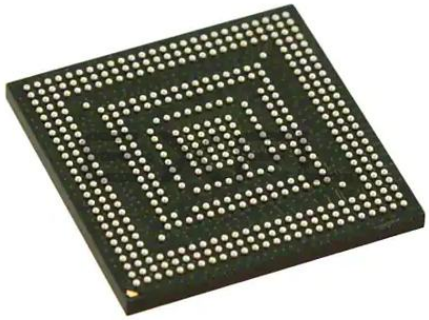

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	ARM1136JF-S
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	532MHz
Co-Processors/DSP	Multimedia; GPU, IPU, MPEG-4, VFP
RAM Controllers	DDR
Graphics Acceleration	Yes
Display & Interface Controllers	Keyboard, Keypad, LCD
Ethernet	-
SATA	-
USB	USB 2.0 (3)
Voltage - I/O	1.8V, 2.0V, 2.5V, 2.7V, 3.0V
Operating Temperature	0°C ~ 70°C (TA)
Security Features	Random Number Generator, RTIC, Secure Fusebox, Secure JTAG, Secure Memory
Package / Case	457-LFBGA
Supplier Device Package	457-LFBGA (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx31vkn5b

1.2 Ordering Information

Table 1 provides the ordering information for the MCIMX31.

Table 1. Ordering Information

Part Number	Silicon Revision[1, 2, 3,4]	Device Mask	Operating Temperature Range (°C)	Package[5]
MCIMX31VKN5	1.15	2L38W and 3L38W	0 to 70	14 x 14 mm, 0.5 mm pitch, MAPBGA-457, Case 1581
MCIMX31LVKN5	1.15	2L38W and 3L38W	0 to 70	
MCIMX31VKN5B	1.2	M45G	0 to 70	
MCIMX31LVKN5B	1.2	M45G	0 to 70	
MCIMX31VKN5C	2.0	M91E	0 to 70	14 x 14 mm, 0.5 mm pitch, MAPBGA-457, Case 1581
MCIMX31LVKN5C	2.0	M91E	0 to 70	
MCIMX31CVKN5C	2.0	M91E	–40 to 85	
MCIMX31LCVKN5C	2.0	M91E	–40 to 85	
MCIMX31VMN5C	2.0	M91E	0 to 70	19 x 19 mm, 0.8 mm pitch, Case 1931
MCIMX31LVMN5C	2.0	M91E	0 to 70	

1 Information on reading the silicon revision register can be found in the IC Identification (IIM) chapter of the Reference Manual, see Section 7, "Product Documentation."

2 Errata and fix information of the various mask sets can be found in the standard MCIMX31 Chip Errata, see Section 7, "Product Documentation."

3 Changes in output buffer characteristics can be found in the I/O Setting Exceptions and Special Pad Descriptions table in the Reference Manual, see Section 7, "Product Documentation."

4 JTAG functionality is not tested nor guaranteed at -40°C.

5 Case 1581 and 1931 are RoHS compliant, lead-free, MSL = 3, and solders at 260°C.

1.2.1 Feature Differences Between Mask Sets

The following is a summary of differences between silicon Revision 2.0, mask set M91E, and previous revisions of silicon. A complete list of these differences is given in Table 72.

- Extended operating temperature range is available: –40°C to 85°C
- Supply current information changes, as shown in Table 13 and Table 14
- FUSE_VDD supply voltage is floated or grounded during read operation
- No restriction on PLL versus core supply voltage
- Operating frequency as shown in Table 8.

3 Signal Descriptions

Signal descriptions are in the reference manual. Special signal considerations are listed following this paragraph. The BGA ball assignment is in Section 5, "Package Information and Pinout."

Special Signal Considerations:

- **Tamper detect (GPIO1_6)**

  Tamper detect logic is used to issue a security violation. This logic is activated if the tamper detect input is asserted.

  The tamper detect logic is disabled after reset. After enabling the logic, it is impossible to disable it until the next reset. The GPR[16] bit functions as the tamper detect enable bit.

  GPIO1_6 functions similarly to other I/O with GPIO capabilities regardless of the status of the tamper detect enable bit. (For example, the GPIO1_6 can function as an input with GPIO capabilities, such as sampling through PSR or generating interrupts.)

- **Power ready (GPIO1_5)**

  The power ready input, GPIO1_5, should be connected to an external power management IC power ready output signal. If not used, GPIO1_5 must either be (a) externally pulled-up to NVCC1 or (b) a no connect, internally pulled-up by enabling the on-chip pull-up resistor. GPIO1_5 is a dedicated input and cannot be used as a general-purpose input/output.

- **SJC_MOD**

  SJC_MOD must be externally connected to GND for normal operation. Termination to GND through an external pull-down resistor (such as 1 kΩ) is allowed, but the value should be much smaller than the on-chip 100 kΩ pull-up.

- **CE_CONTROL**

  CE_CONTROL is a reserved input and must be externally tied to GND through a 1 kΩ resistor.

- **TTM_PAD**

  TTM_PAD is for Freescale factory use only. Control bits indicate pull-up/down disabled. However, TTM_PAD is actually connected to an on-chip pull-down device. Users must either float this signal or tie it to GND.

- **M_REQUEST and M_GRANT**

  These two signals are not utilized internally. The user should make no connection to these signals.

- **Clock Source Select (CLKSS)**

  The CLKSS is the input that selects the default reference clock source providing input to the DPLL. To select CKIH, tie CLKSS to NVCC1. To select CKIL, tie CLKSS to ground. After initialization, the reference clock source can be changed (initial setting is overwritten) by programming the PRCS bits in the CCMR.

4 Electrical Characteristics

This section provides the device-level and module-level electrical characteristics for the MCIMX31.

4.1 Chip-Level Conditions

This section provides the device-level electrical characteristics for the IC. See Table 4 for a quick reference to the individual tables and sections.

Table 4. MCIMX31 Chip-Level Conditions

For these characteristics, …	Topic appears …
Table 5, “Absolute Maximum Ratings”	on page 10
Table 7, “Thermal Resistance Data—19 × 19 mm Package”	on page 11
Table 8, “Operating Ranges”	on page 13
Table 9, “Specific Operating Ranges for Silicon Revision 2.0”	on page 14
Table 10, “Interface Frequency”	on page 14
Section 4.1.1, “Supply Current Specifications”	on page 16
Section 4.2, “Supply Power-Up/Power-Down Requirements and Restrictions”	on page 19

CAUTION

Stresses beyond those listed under Table 5 may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated under Table 8, "Operating Ranges," on page 13 is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Table 5. Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Units
Supply Voltage (Core)	$QVCC_{max}$	–0.5	1.65	V
Supply Voltage (I/O)	$NVCC_{max}$	–0.5	3.3	V
Input Voltage Range	V_{Imax}	–0.5	NVCC +0.3	V
Storage Temperature	$T_{storage}$	–40	125	°C
ESD Damage Immunity:				
Human Body Model (HBM)	V_{esd}	—	1500	V
Machine Model (MM)		—	200	
Charge Device Model (CDM)		—	500	
Offset voltage allowed in run mode between core supplies.	V_{core_offset} [1]	—	15	mV

[1] The offset is the difference between all core voltage pair combinations of QVCC, QVCC1, and QVCC4.

Table 6 provides the thermal resistance data for the 14 × 14 mm, 0.5 mm pitch package.

Table 6. Thermal Resistance Data—14 × 14 mm Package

Rating	Board	Symbol	Value	Unit	Notes
Junction to Ambient (natural convection)	Single layer board (1s)	$R_{\theta JA}$	56	°C/W	1, 2, 3
Junction to Ambient (natural convection)	Four layer board (2s2p)	$R_{\theta JA}$	30	°C/W	1, 3
Junction to Ambient (@200 ft/min)	Single layer board (1s)	$R_{\theta JMA}$	46	°C/W	1, 2, 3
Junction to Ambient (@200 ft/min)	Four layer board (2s2p)	$R_{\theta JMA}$	26	°C/W	1, 3
Junction to Board	—	$R_{\theta JB}$	17	°C/W	1, 4
Junction to Case	—	$R_{\theta JC}$	10	°C/W	1, 5
Junction to Package Top (natural convection)	—	Ψ_{JT}	2	°C/W	1, 6

NOTES

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

Table 7 provides the thermal resistance data for the 19 × 19 mm, 0.8 mm pitch package.

Table 7. Thermal Resistance Data—19 × 19 mm Package

Rating	Board	Symbol	Value	Unit	Notes
Junction to Ambient (natural convection)	Single layer board (1s)	$R_{\theta JA}$	46	°C/W	1, 2, 3
Junction to Ambient (natural convection)	Four layer board (2s2p)	$R_{\theta JA}$	29	°C/W	1, 2, 3
Junction to Ambient (@200 ft/min)	Single layer board (1s)	$R_{\theta JMA}$	38	°C/W	1, 2, 3
Junction to Ambient (@200 ft/min)	Four layer board (2s2p)	$R_{\theta JMA}$	25	°C/W	1, 2, 3
Junction to Board	—	$R_{\theta JB}$	19	°C/W	1, 3
Junction to Case (Top)	—	$R_{\theta JCtop}$	10	°C/W	1, 4
Junction to Package Top (natural convection)	—	Ψ_{JT}	2	°C/W	1, 5

4.2 Supply Power-Up/Power-Down Requirements and Restrictions

Any MCIMX31 board design must comply with the power-up and power-down sequence guidelines as described in this section to guarantee reliable operation of the device. Any deviation from these sequences may result in any or all of the following situations:

- Cause excessive current during power up phase
- Prevent the device from booting
- Cause irreversible damage to the MCIMX31 (worst-case scenario)

4.2.1 Powering Up

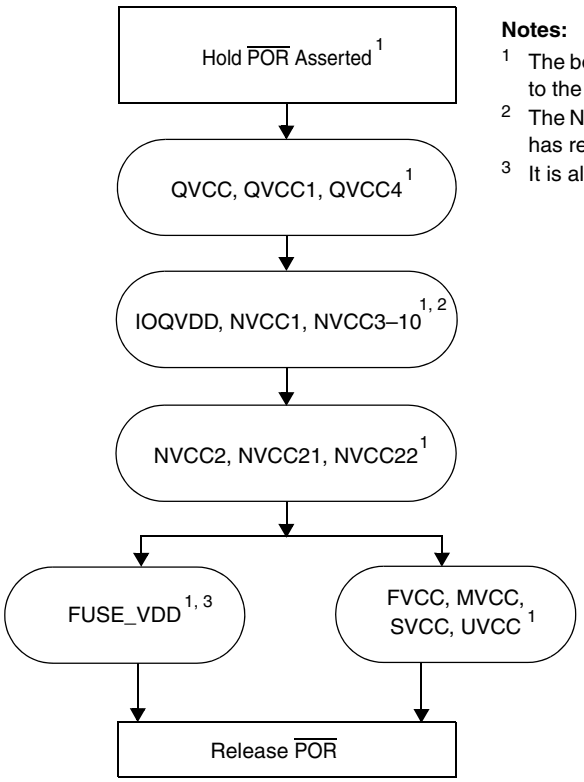
The Power On Reset ($\overline{\text{POR}}$) pin must be kept asserted (low) throughout the power up sequence. Power up logic must guarantee that all power sources reach their target values prior to the release (de-assertion) of $\overline{\text{POR}}$. Figure 2 shows the power-up sequence for silicon Revisions 1.2 and previous. Figure 3 and Figure 4 show the power-up sequence for silicon Revision 2.0.

NOTE

Stages need to be performed in the order shown; however, *within* each stage, supplies can be powered up in any order. For example, supplies IOQVDD, NVCC1, and NVCC3 through NVCC10 do not need to be powered up in the order shown.

CAUTION

NVCC6 and NVCC9 must be at the same voltage potential. These supplies are connected together on-chip to optimize ESD damage immunity.



Notes:

1. The board design must guarantee that supplies reach 90% level before transition to the next state, using Power Management IC or other means.
2. The NVCC1 supply must not precede IOQVDD by more than 0.2 V until IOQVDD has reached 1.5 V. If IOQVDD is powered up first, there are no restrictions.
3. It is allowable for FVCC, MVCC, SVCC, and UVCC to be up after FUSE_VDD.

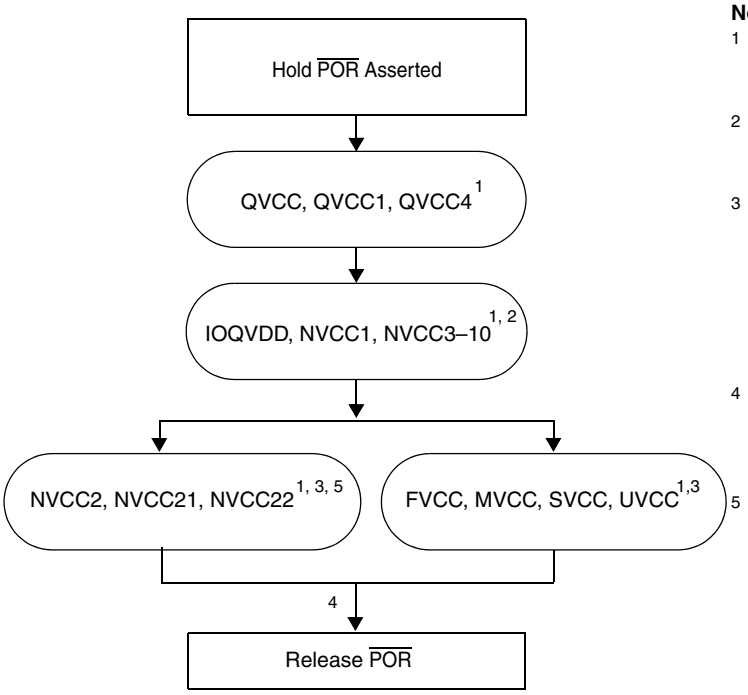
Figure 2. Power-Up Sequence for Silicon Revisions 1.2 and Previous

4.2.1.1 Power-Up Sequence for Silicon Revision 2

Silicon revision 2.0 offers two options for power-up sequencing. Option 1 is backwards compatible with silicon revision 1.2 and earlier versions of the IC. It should be noted that using option 1 on silicon Rev. 2.0 introduces a slight increase in current drain on IOQVDD when IOQVDD is raised before NVCC21. The expected resulting increase is in the range of 3 mA to 5 mA, which does not pose a risk to the IC.

Option 2 is an alternative power-up sequence that allows the powering up of NVCC2, NVCC21, NVCC22 with IOQVDD, NVCC1, and NVCC3-10 without producing a current drain increase on IOQVDD.

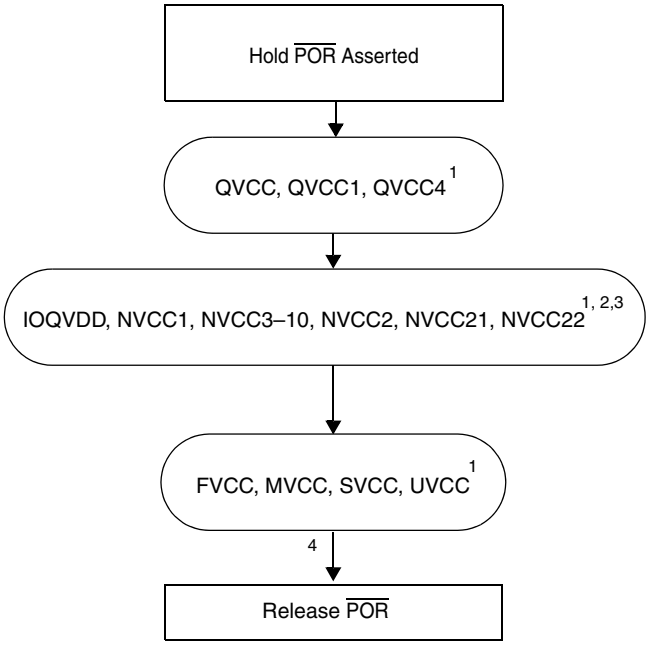
These two power-up options on the 2.0 silicon allow the user to select the optimum power-up sequence for their application.



Notes:

1. The board design must guarantee that supplies reach 90% level before transition to the next state, using Power Management IC or other means.
2. The NVCC1 supply must not precede IOQVDD by more than 0.2 V until IOQVDD has reached 1.5 V. If IOQVDD is powered up first, there are no restrictions.
3. The parallel paths in the flow indicate that supply group NVCC2, NVCC21, and NVCC22, and supply group FVCC, MVCC, SVCC, and UVCC ramp-ups are independent. Note that this power-up sequence is backward compatible to Silicon Revs. 1.15 and 1.2, because NVCC2x ramp-up proceeding PLL supplies is allowed.
4. Unlike the power-up sequence for Silicon Revision 1.2, FUSE_VDD should not be driven on power-up for Silicon Revision 2.0. This supply is dedicated for fuse burning (programming), and should not be driven upon boot-up.
5. Raising IOQVDD before NVCC21 produces a slight increase in current drain on IOQVDD of approximately 3–5 mA. The current increase will not damage the IC. Refer to Errata ID TLSbo91750 for details.

Figure 3. Option 1 Power-Up Sequence (Silicon Revision 2.0)



Notes:

1. The board design must guarantee that supplies reach 90% level before transition to the next state, using Power Management IC or other means.
2. The NVCC1 supply must not precede IOQVDD by more than 0.2 V until IOQVDD has reached 1.5 V. If IOQVDD is powered up first, there are no restrictions.
3. Raising NVCC2, NVCC21, and NVCC22 at the same time as IOQVDD does not produce the slight increase in current drain on IOQVDD (as described in Figure 3, Note 5).
4. Unlike the power-up sequence for Silicon Revision 1.2, FUSE_VDD should not be driven on power-up for Silicon Revision 2.0. This supply is dedicated for fuse burning (programming), and should not be driven upon boot-up.

Figure 4. Option 2 Power-Up Sequence (Silicon Revision 2.0)

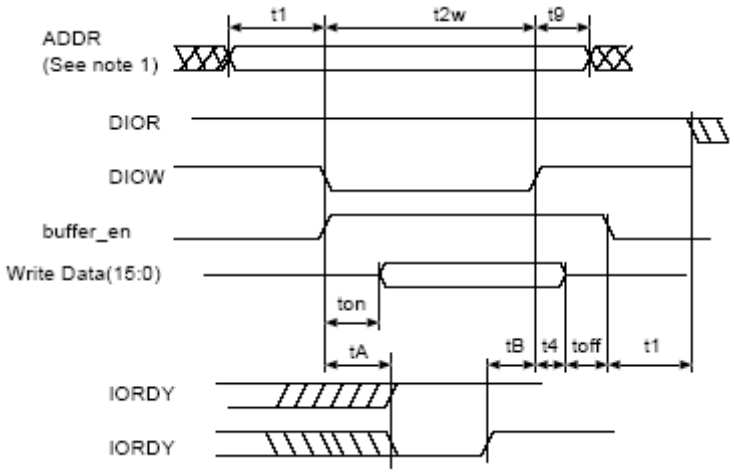


Figure 12. Multiword DMA (MDMA) Timing

Table 26. PIO Write Timing Parameters

ATA Parameter	Parameter from Figure 12	Value	Controlling Variable
t1	t1	t1 (min) = time_1 * T – (tskew1 + tskew2 + tskew5)	time_1
t2	t2w	t2 (min) = time_2w * T – (tskew1 + tskew2 + tskew5)	time_2w
t9	t9	t9 (min) = time_9 * T – (tskew1 + tskew2 + tskew6)	time_9
t3	—	t3 (min) = (time_2w – time_on)* T – (tskew1 + tskew2 +tskew5)	If not met, increase time_2w
t4	t4	t4 (min) = time_4 * T – tskew1	time_4
tA	tA	tA = (1.5 + time_ax) * T – (tco + tsui + tcable2 + tcable2 + 2*tbuf)	time_ax
t0	—	t0(min) = (time_1 + time_2 + time_9) * T	time_1, time_2r, time_9
—	—	Avoid bus contention when switching buffer on by making ton long enough.	—
—	—	Avoid bus contention when switching buffer off by making toff long enough.	—

Figure 13 shows timing for MDMA read, Figure 14 shows timing for MDMA write, and Table 27 lists the timing parameters for MDMA read and write.

4.3.5.3 UDMA In Timing

Figure 15 shows timing when the UDMA in transfer starts, Figure 16 shows timing when the UDMA in host terminates transfer, Figure 17 shows timing when the UDMA in device terminates transfer, and Table 28 lists the timing parameters for UDMA in burst.

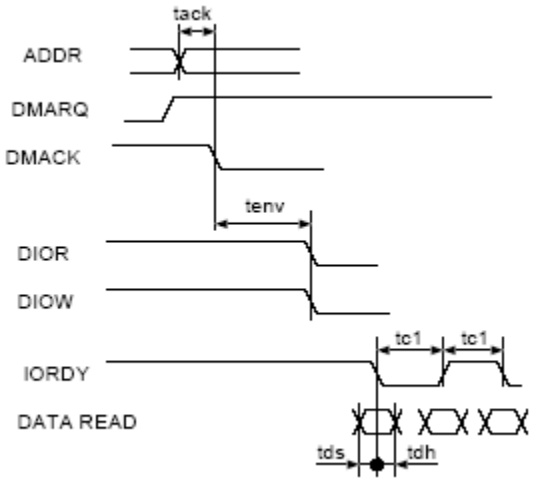


Figure 15. UDMA In Transfer Starts Timing Diagram

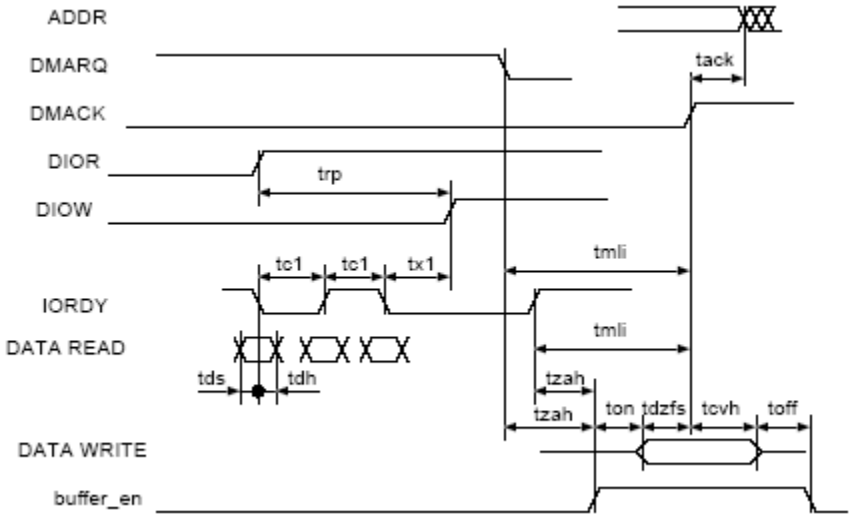


Figure 16. UDMA In Host Terminates Transfer Timing Diagram

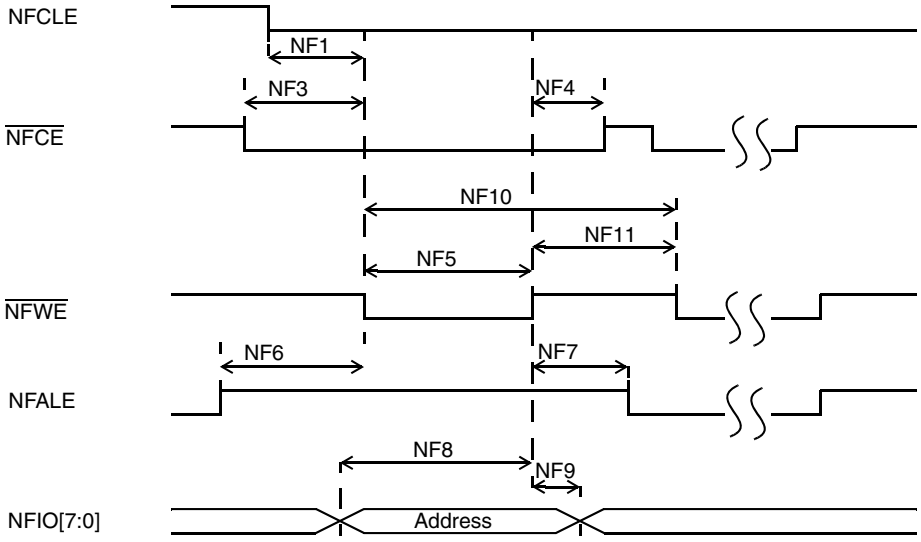


Figure 24. Address Latch Cycle Timing Diagram

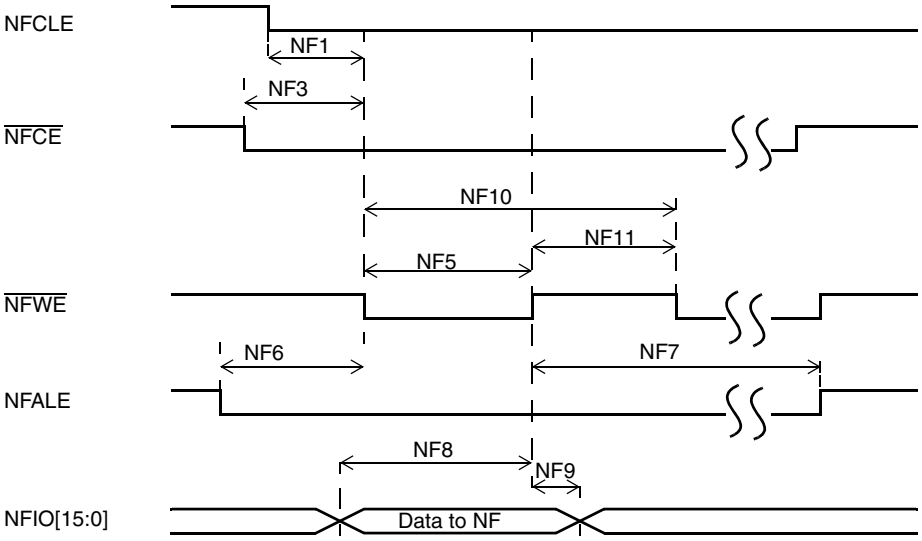
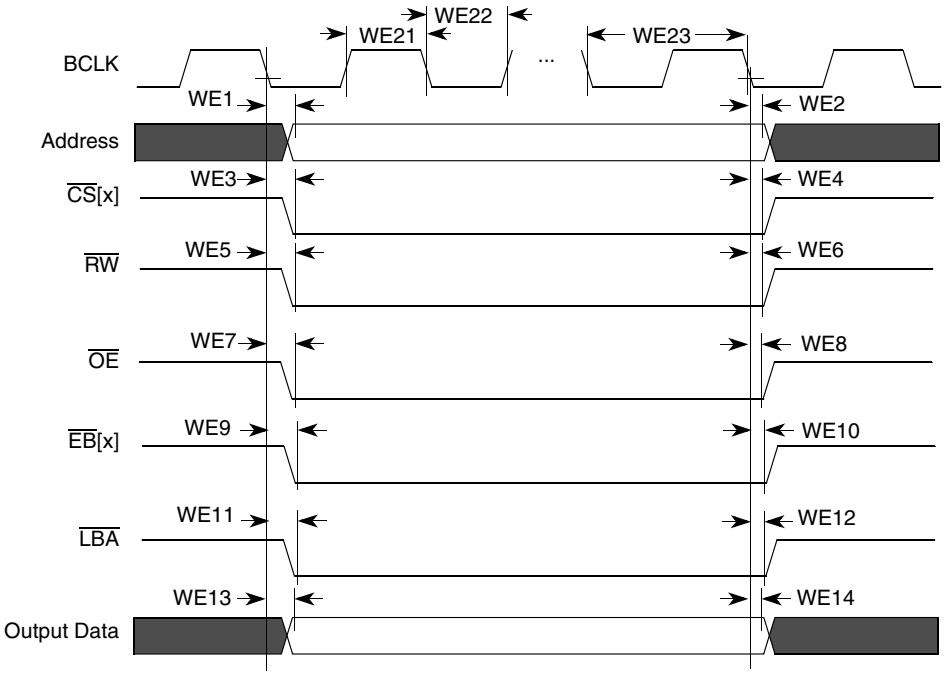


Figure 25. Write Data Latch Cycle Timing Diagram

WEIM Outputs Timing



WEIM Inputs Timing

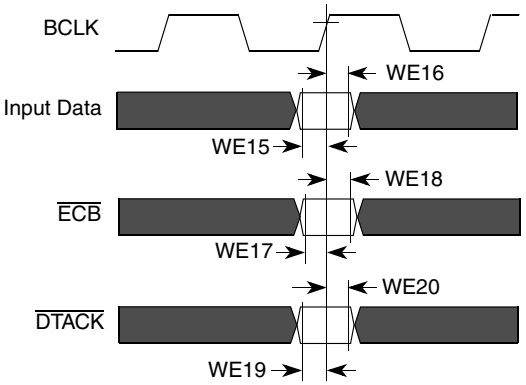


Figure 27. WEIM Bus Timing Diagram

Table 33. WEIM Bus Timing Parameters

ID	Parameter	Min	Max	Unit
WE1	Clock fall to Address Valid	–0.5	2.5	ns
WE2	Clock rise/fall to Address Invalid	–0.5	5	ns
WE3	Clock rise/fall to $\overline{CS}$[x] Valid	–3	3	ns
WE4	Clock rise/fall to $\overline{CS}$[x] Invalid	–3	3	ns
WE5	Clock rise/fall to $\overline{RW}$ Valid	–3	3	ns
WE6	Clock rise/fall to $\overline{RW}$ Invalid	–3	3	ns
WE7	Clock rise/fall to $\overline{OE}$ Valid	–3	3	ns

Table 46. Supported Display Components[1]

Type	Vendor	Model
TFT displays (memory-less)	Sharp (HR-TFT Super Mobile LCD family)	LQ035Q7 DB02, LM019LC1Sxx
	Samsung (QCIF and QVGA TFT modules for mobile phones)	LTS180S1-HF1, LTS180S3-HF1, LTS350Q1-PE1, LTS350Q1-PD1, LTS220Q1-HE1[2]
	Toshiba (LTM series)	LTM022P806[2], LTM04C380K[2], LTM018A02A[2], LTM020P332[2], LTM021P337[2], LTM019P334[2], LTM022A783[2], LTM022A05ZZ[2]
	NEC	NL6448BC20-08E, NL8060BC31-27
Display controllers	Epson	S1D15xxx series, S1D19xxx series, S1D13713, S1D13715
	Solomon Systech	SSD1301 (OLED), SSD1828 (LDCD)
	Hitachi	HD66766, HD66772
	ATI	W2300
Smart display modules	Epson	L1F10043 T[2], L1F10044 T[2], L1F10045 T[2], L2D22002[2], L2D20014[2], L2F50032[2], L2D25001 T[2]
	Hitachi	120 160 65K/4096 C-STN (#3284 LTD-1398-2) based on HD 66766 controller
	Densitron Europe LTD	All displays with MPU 80/68K series interface and serial peripheral interface
	Sharp	LM019LC1Sxx
	Sony	ACX506AKM
Digital video encoders (for TV)	Analog Devices	ADV7174/7179
	Crystal (Cirrus Logic)	CS49xx series
	Focus	FS453/4

1 Freescale Semiconductor does not recommend one supplier over another and in no way suggests that these are the only display component suppliers.

2 These display components not validated at time of publication.

4.3.15.2 Synchronous Interfaces

4.3.15.2.1 Interface to Active Matrix TFT LCD Panels, Functional Description

Figure 46 depicts the LCD interface timing for a generic active matrix color TFT panel. In this figure signals are shown with negative polarity. The sequence of events for active matrix interface timing is:

- DISPB_D3_CLK latches data into the panel on its negative edge (when positive polarity is selected). In active mode, DISPB_D3_CLK runs continuously.
- DISPB_D3_HSYNC causes the panel to start a new line.
- DISPB_D3_VSYNC causes the panel to start a new frame. It always encompasses at least one HSYNC pulse.

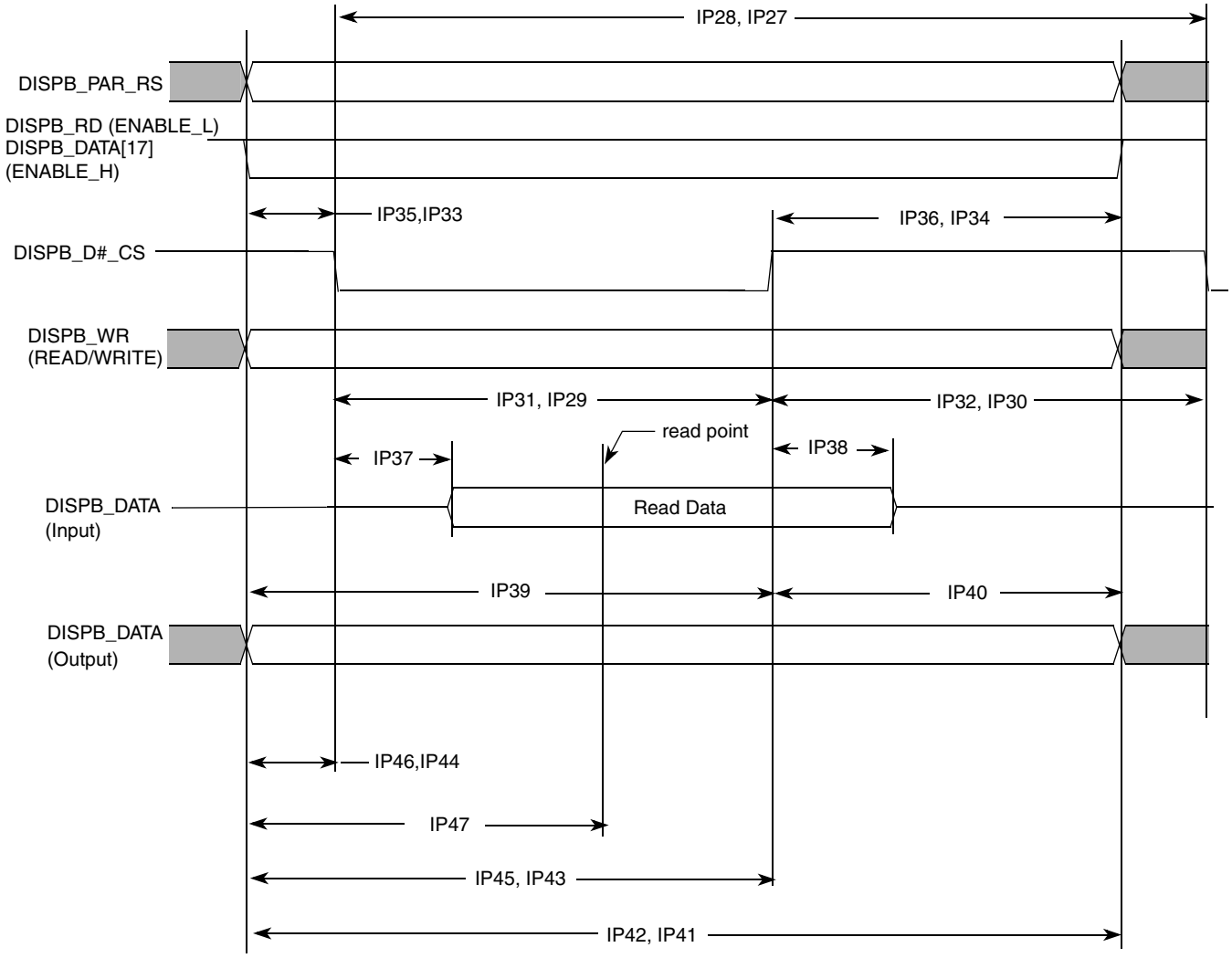


Figure 59. Asynchronous Parallel System 68k Interface (Type 1) Timing Diagram

4.3.15.5.4 Serial Interfaces, Electrical Characteristics

Figure 65 depicts timing of the serial interface. Table 51 lists the timing parameters at display access level.

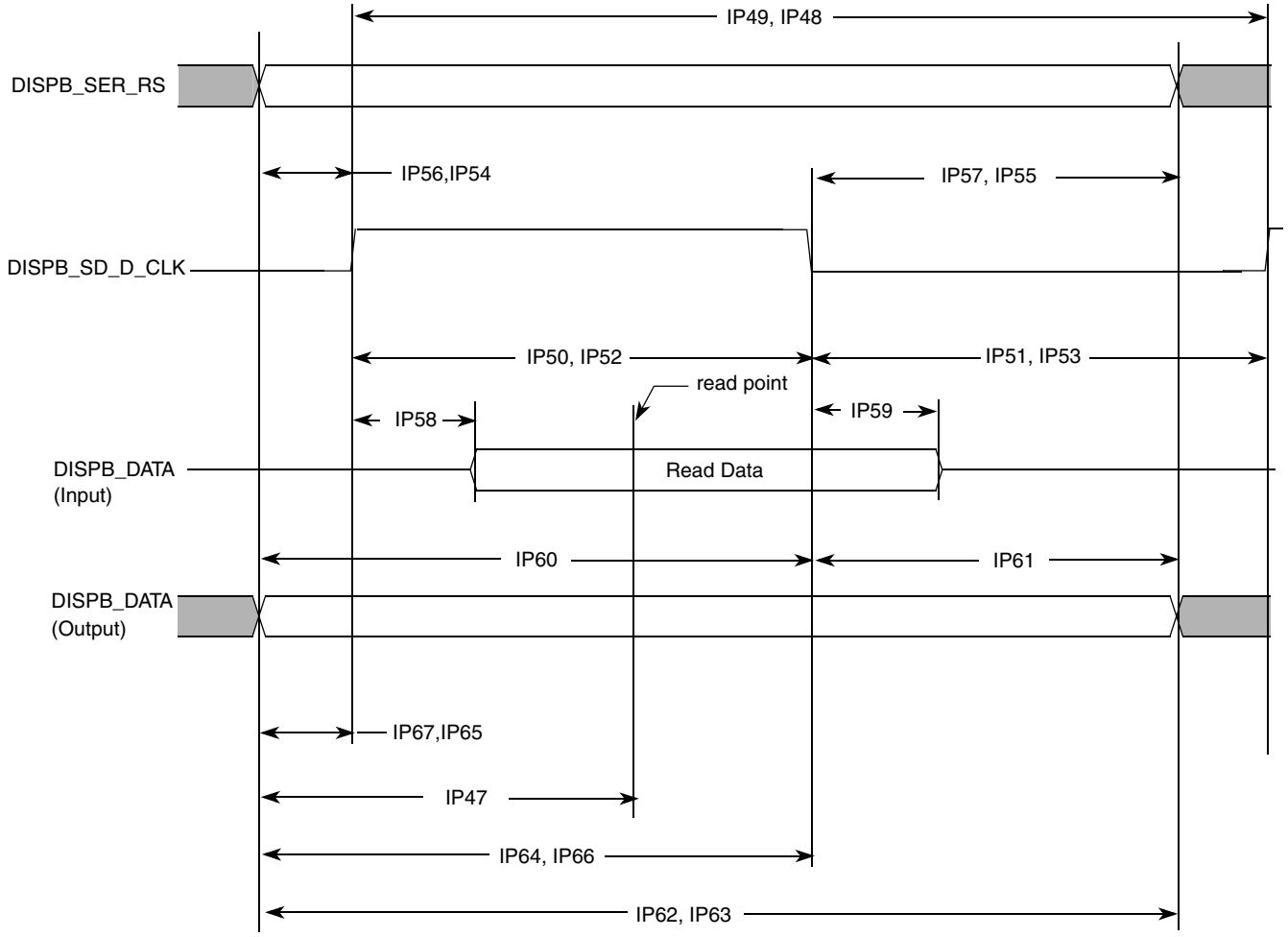


Figure 65. Asynchronous Serial Interface Timing Diagram

Table 51. Asynchronous Serial Interface Timing Parameters—Access Level

ID	Parameter	Symbol	Min.	Typ.[1]	Max.	Units
IP48	Read system cycle time	Tcycr	Tdicpr–1.5	Tdicpr[2]	Tdicpr+1.5	ns
IP49	Write system cycle time	Tcycw	Tdicpw–1.5	Tdicpw[3]	Tdicpw+1.5	ns
IP50	Read clock low pulse width	Trl	Tdicdr–Tdicur–1.5	Tdicdr[4]–Tdicur[5]	Tdicdr–Tdicur+1.5	ns
IP51	Read clock high pulse width	Trh	Tdicpr–Tdicdr+Tdicur–1.5	Tdicpr–Tdicdr+ Tdicur	Tdicpr–Tdicdr+Tdicur+1.5	ns
IP52	Write clock low pulse width	Twl	Tdicdw–Tdicuw–1.5	Tdicdw[6]–Tdicuw[7]	Tdicdw–Tdicuw+1.5	ns
IP53	Write clock high pulse width	Twh	Tdicpw–Tdicdw+ Tdicuw–1.5	Tdicpw–Tdicdw+ Tdicuw	Tdicpw–Tdicdw+ Tdicuw+1.5	ns
IP54	Controls setup time for read	Tdcsr	Tdicur–1.5	Tdicur	—	ns
IP55	Controls hold time for read	Tdchr	Tdicpr–Tdicdr–1.5	Tdicpr–Tdicdr	—	ns

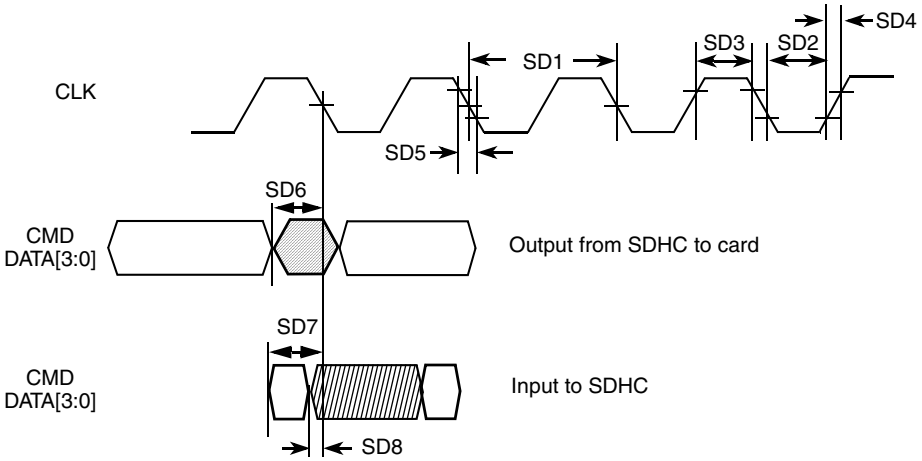


Figure 72. SDHC Timing Diagram

Table 56. SDHC Interface Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
Card Input Clock					
SD1	Clock Frequency (Low Speed)	f_{PP}[1]	0	400	kHz
	Clock Frequency (SD/SDIO Full Speed)	f_{PP}[2]	0	25	MHz
	Clock Frequency (MMC Full Speed)	f_{PP}[3]	0	20	MHz
	Clock Frequency (Identification Mode)	f_{OD}[4]	100	400	kHz
SD2	Clock Low Time	t_{WL}	10	—	ns
SD3	Clock High Time	t_{WH}	10	—	ns
SD4	Clock Rise Time	t_{TLH}	—	10	ns
SD5	Clock Fall Time	t_{THL}	—	10	ns
SDHC Output/Card Inputs CMD, DAT (Reference to CLK)					
SD6	SDHC output delay	t_{ODL}	–6.5	3	ns
SDHC Input/Card Outputs CMD, DAT (Reference to CLK)					
SD7	SDHC input setup	t_{IS}	—	18.5	ns
SD8	SDHC input hold	t_{IH}	—	–11.5	ns

1 In low speed mode, card clock must be lower than 400 kHz, voltage ranges from 2.7 V–3.3 V.
2 In normal data transfer mode for SD/SDIO card, clock frequency can be any value between 0 MHz–25 MHz.
3 In normal data transfer mode for MMC card, clock frequency can be any value between 0 MHz–20 MHz.
4 In card identification mode, card clock must be 100 kHz–400 kHz, voltage ranges from 2.7 V–3.3 V.

4.3.20 SIM Electrical Specifications

Each SIM card interface consist of a total of 12 pins (for 2 separate ports of 6 pins each. Mostly one port with 5 pins is used).

The interface is meant to be used with synchronous SIM cards. This means that the SIM module provides a clock for the SIM card to use. The frequency of this clock is normally 372 times the data rate on the TX/RX pins, however SIM module can work with CLK equal to 16 times the data rate on TX/RX pins.

There is no timing relationship between the clock and the data. The clock that the SIM module provides to the aim card will be used by the SIM card to recover the clock from the data much like a standard UART. All six (or 5 in case bi-directional TXRX is used) of the pins for each half of the SIM module are asynchronous to each other.

There are no required timing relationships between the signals in normal mode, but there are some in two specific cases: reset and power down sequences.

4.3.20.1 General Timing Requirements

Figure 73 shows the timing of the SIM module, and Figure 57 lists the timing parameters.

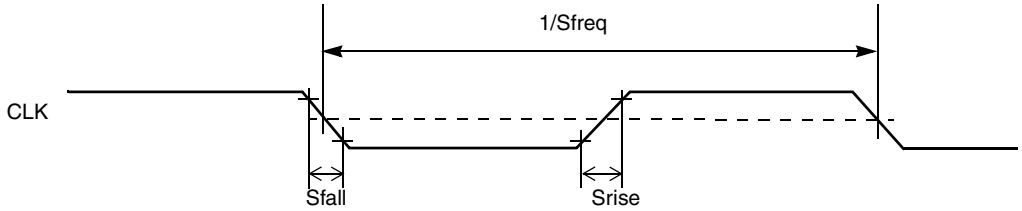


Figure 73. SIM Clock Timing Diagram

Table 57. SIM Timing Specification—High Drive Strength

Num	Description	Symbol	Min	Max	Unit
1	SIM Clock Frequency (CLK)[1]	S_{freq}	0.01	5 (Some new cards may reach 10)	MHz
2	SIM CLK Rise Time [2]	S_{rise}	—	20	ns
3	SIM CLK Fall Time [3]	S_{fall}	—	20	ns
4	SIM Input Transition Time (RX, SIMPD)	S_{trans}	—	25	ns

1 50% duty cycle clock
2 With C = 50pF
3 With C = 50pF

4.3.20.2 Reset Sequence

4.3.20.2.1 Cards with Internal Reset

The sequence of reset for this kind of SIM Cards is as follows (see Figure 74):

- After powerup, the clock signal is enabled on SGCLK (time T0)
- After 200 clock cycles, RX must be high.
- The card must send a response on RX acknowledging the reset between 400 and 40000 clock cycles after T0.

4.3.20.3 Power Down Sequence

Power down sequence for SIM interface is as follows:

1. SIMPD port detects the removal of the SIM Card
2. RST goes Low
3. CLK goes Low
4. TX goes Low
5. VEN goes Low

Each of this steps is done in one CKIL period (usually 32 kHz). Power down can be started because of a SIM Card removal detection or launched by the processor. Figure 76 and Table 58 show the usual timing requirements for this sequence, with Fckil = CKIL frequency value.

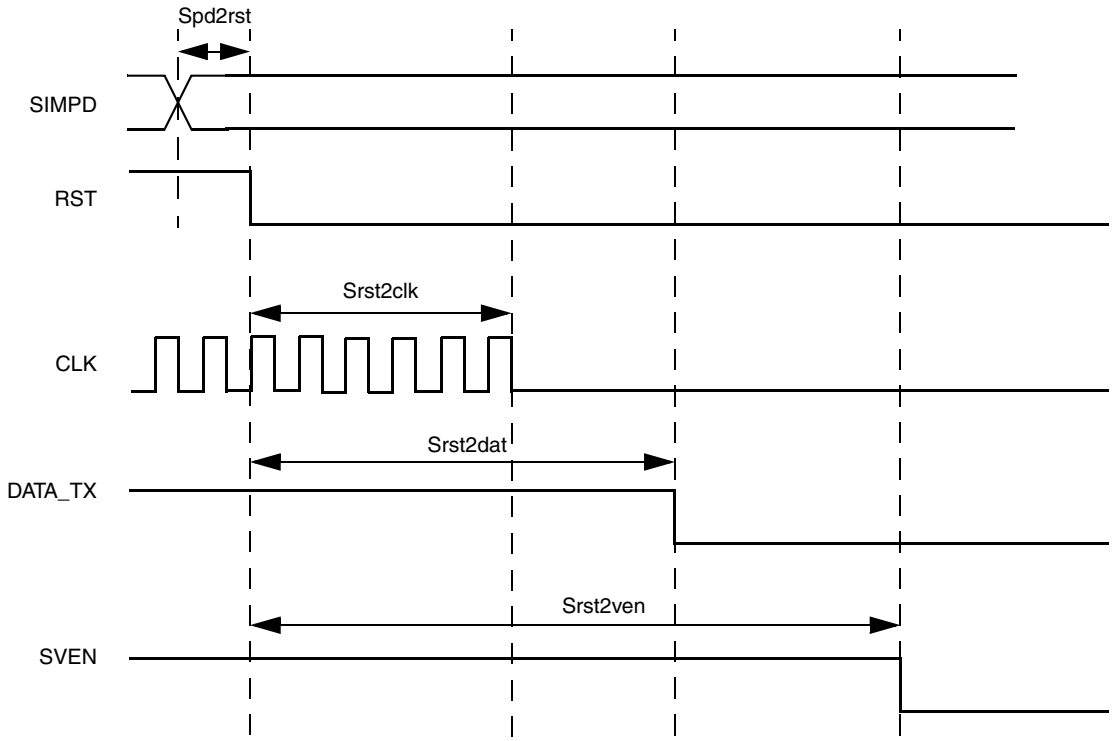


Figure 76. SmartCard Interface Power Down AC Timing

Table 58. Timing Requirements for Power Down Sequence

Num	Description	Symbol	Min	Max	Unit
1	SIM reset to SIM clock stop	$S_{rst2clk}$	0.9*1/FCKIL	0.8	µs
2	SIM reset to SIM TX data low	$S_{rst2dat}$	1.8*1/FCKIL	1.2	µs
3	SIM reset to SIM Voltage Enable Low	$S_{rst2ven}$	2.7*1/FCKIL	1.8	µs
4	SIM Presence Detect to SIM reset Low	S_{pd2rst}	0.9*1/FCKIL	25	ns

4.3.22.4 SSI Receiver Timing with External Clock

Figure 84 depicts the SSI receiver timing with external clock, and Table 63 lists the timing parameters.

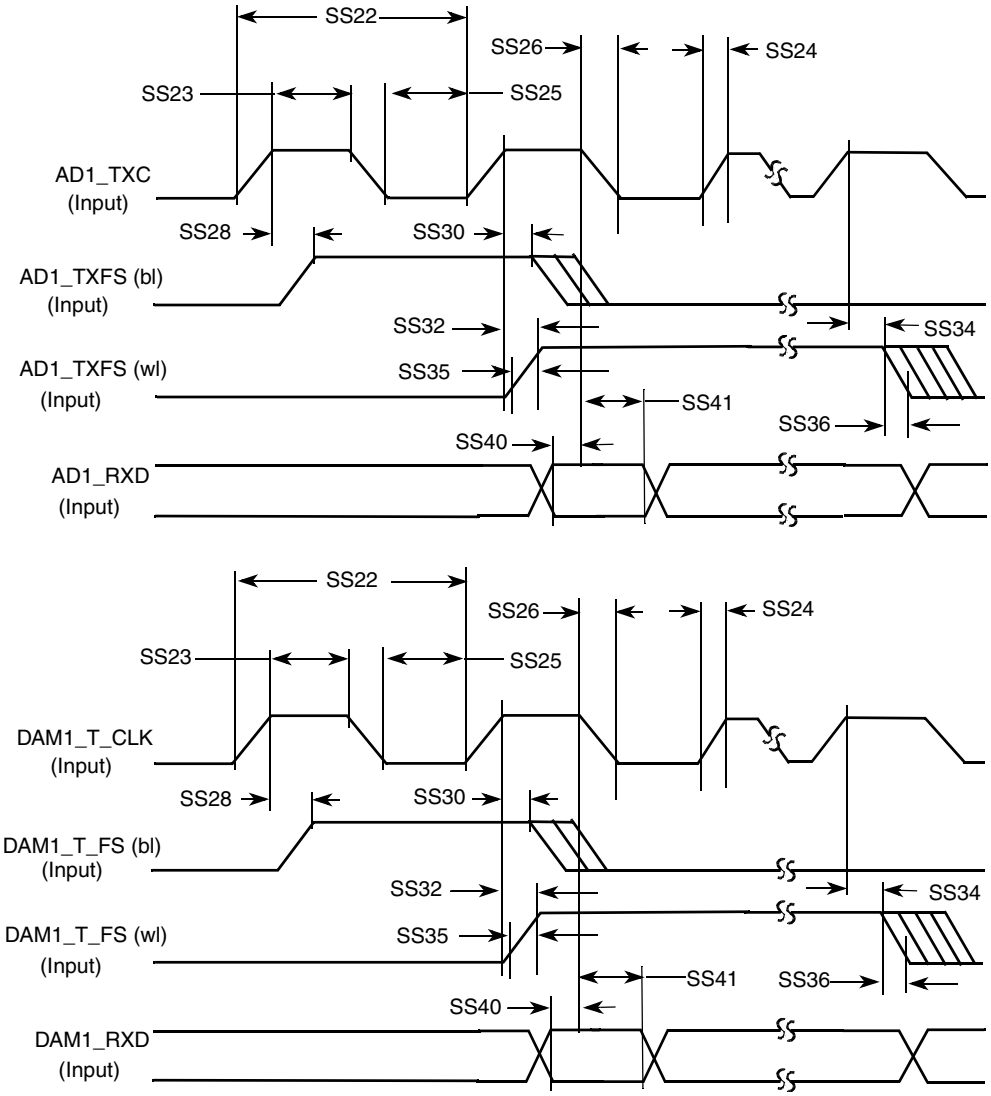


Figure 84. SSI Receiver with External Clock Timing Diagram

Table 63. SSI Receiver with External Clock Timing Parameters

ID	Parameter	Min	Max	Unit
External Clock Operation				
SS22	(Tx/Rx) CK clock period	81.4	—	ns
SS23	(Tx/Rx) CK clock high period	36.0	—	ns
SS24	(Tx/Rx) CK clock rise time	—	6.0	ns
SS25	(Tx/Rx) CK clock low period	36.0	—	ns
SS26	(Tx/Rx) CK clock fall time	—	6.0	ns

5 Package Information and Pinout

This section includes the contact assignment information and mechanical package drawing for the MCIMX31.

5.1 MAPBGA Production Package—457 14 x 14 mm, 0.5 mm Pitch

This section contains the outline drawing, signal assignment map (see Section 8, "Revision History," Table 70 for the 0.5 mm 14 × 14 MAPBGA signal assignments), and MAPBGA ground/power ID by ball grid location for the 457 14 x 14 mm, 0.5 mm pitch package.

5.1.1 Production Package Outline Drawing–14 x 14 mm 0.5 mm

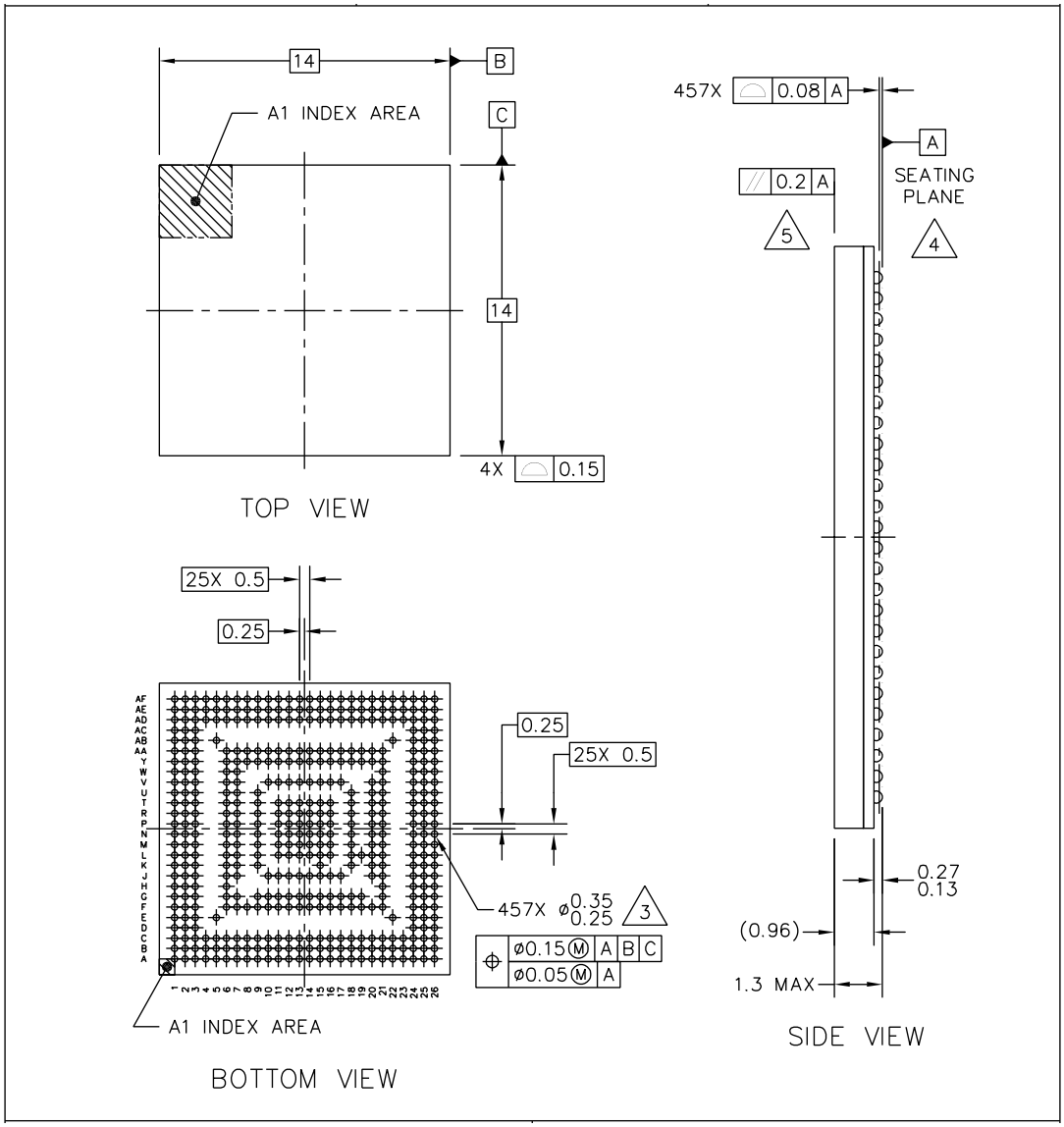


Figure 86. Production Package: Case 1581—0.5 mm Pitch

Table 73. Product Differentiation (continued)

Item	Location	MCIMX31/MCIMX31L	MCIMX31C/MCIMX31LC
GPIO maximum input current (100 kΩ PU)	Table 15, "GPIO DC Electrical Parameters," on page 22	V_I = 0, I_{IN} = 25 μA V_I = NVCC, I_{IN} = 0.1 μA	N/A N/A
Core operating speed	Table 8, "Operating Ranges," on page 13	532 MHz	400 MHz
Package	Table 70, "Ball Map—14 x 14 0.5 mm Pitch," on page 117 and Table 71, "Ball Map—19 x 19 0.8 mm Pitch," on page 118	MAPBGA Packages 457 14 x 14 mm, 0.5 mm Pitch 473 19 x 19 mm, 0.8 mm Pitch	MAPBGA Package 473 19 x 19 mm, 0.8 mm Pitch
Pin Assignment	Table 66, "14 x 14 BGA Signal ID by Ball Grid Location," on page 107 and Table 69, "19 x 19 BGA Signal ID by Ball Grid Location," on page 113	MAPBGA Packages 457 14 x 14 mm, 0.5 mm Pitch 473 19 x 19 mm, 0.8 mm Pitch	MAPBGA Package 473 19 x 19 mm, 0.8 mm Pitch

7 Product Documentation

This Data Sheet is labeled as a particular type: Product Preview, Advance Information, or Technical Data. Definitions of these types are available at: http://www.freescale.com.

MCIMX31 Product Brief (order number MCIMX31PB)

MCIMX31 Reference Manual (order number MCIMX31RM)

MCIMX31 Chip Errata (order number MCIMX31CE)

The Freescale manuals are available on the Freescale Semiconductors Web site at http://www.freescale.com/imx. These documents may be downloaded directly from the Freescale Web site, or printed versions may be ordered. ARM Ltd. documentation is available from http://www.arm.com.

8 Revision History

Table 74 summarizes revisions to this document since the release of Rev. 3.4.

Table 74. Revision History

Rev.	Location	Revision
4	Figure 87, Table 73	Updated.
4.1	Table 1, "Ordering Information," on page 3	Added note about JTAG compliance.
4.1	Section 1.2.1/3	Updated with new operating frequencies
4.1	Table 8, "Operating Ranges," on page 13	Added new operating frequencies